

Status of DMAPS (WP5) Activities

S. Grinstein (IFAE-Barcelona) and F. Hüggling, N. Wermes (Bonn)

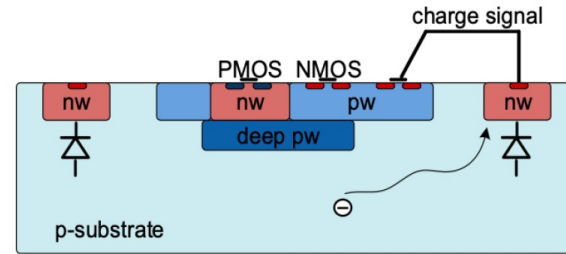
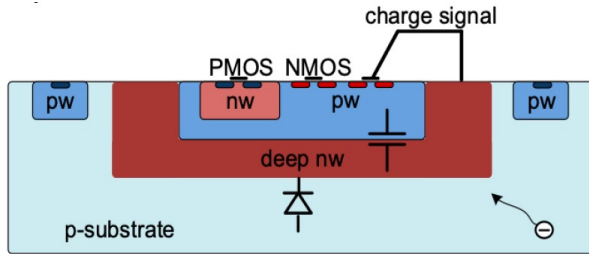
3rd Annual Meeting Valencia – 20 Mar 2024
<https://indico.cern.ch/event/1307202/>



This project has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 101004761.

- 7 projects are (partially, not exclusively) supported by the AIDAInnova framework using 4 different processes provided by 2 foundries: **LFoundry** (Wuxi Xichanweixin Semiconductor) and **TowerJazz** → Tower Semiconductor (Intel as of 2022)
- All developments have samples, characterisation in full swing

large electrode (radhard)



small electrode (high granularity)

Submission	Process	Availability	Target	Comments	Contact Institute	Task Contact
TJ-MALTA 2 /3	TowerJazz 180 nm	Beginning 2021 MPW Q1 2022	High-gran./ Rad. hard Task 5.2/5.3	LHC	CERN	Carlos Solans Sanchez
TJ-Monopix 2 /3 (OBELIX)	TowerJazz 180 nm	Spring 2021 Initiating design	High-granularity Task 5.2	Belle II	Bonn	Jochen Dingfelder
TJ 65	TowerJazz 65 nm	September 2021	High-granularity Task 5.2	Generic R&D / ALICE	IPHC	Jerome Baudot
ARCADIA	LFoundry 110 nm	Summer 2021	High-granularity Task 5.2	Demonstrator chip	INFN	Manuel Rolo
LF-Monopix 2	LFoundry 150 nm	Beginning 2021	Radiation hard Task 5.3	High granularity foreseen	Bonn/CPPM	Marlon Barbero
RD50-MPW 3 /4	LFoundry 150 nm	Spring 2022/ late 2023	High-granularity/ Radiation hard Task 5.3	R&D	Liverpool	Eva Vilella
MiniCactus 1 / 2	LFoundry 150 nm	Beginning 2021 / 2024	Radiation hard Task 5.3	Timing R&D	IRFU	Philippe Schwemling

April 2021

Tasks	Description	Year 1												Year 2												Year 3												Year 4																																			
		1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50																						
WP5: Depleted Monolithic Active Pixel Sensors																																																																									
5.1	Coordination and Communication																																																																								
5.2	Development of high granularity DMAPS													M												D												M												D																							
5.3	Development of radiation hard DMAPS																									M												D												M												D											

Milestones have short associated reports and are within the responsibility of the institutes in the last column.

- Next Milestone is MS19 in April: structures from Arcadia project are available.

MS18	High granularity prototype fabrication 1	5.2	M12	Devices available	CNRS-IPHC
MS19	High granularity prototype fabrication 2	5.2	M36	Devices available	INFN ← April 2024
MS20	Radiation hard prototype fabrication	5.3	M23	Devices available	Bonn
MS21	Test beam of the radiation hard monolithic pixel 1	5.3	M42	Test beam with prototypes measured	CERN

April 2022 ✓ → Feb 2023 ✓

See also: <https://aidainnova.web.cern.ch/wp5>

TJ-MALTA

- JINST 2021 <https://doi.org/10.5281/zenodo.6951327>
- TWEPP 2021 <https://doi.org/10.1088/1748-0221/17/04/C04034>
- IEEE TNS 2022 <https://doi.org/10.1109/TNS.2022.3170729>
- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167390>
- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167226>
- NIM A 2023 <https://doi.org/10.1016/j.nima.2022.167809>
- EPJ-C 2023: <https://doi.org/10.1140/epjc/s10052-023-11760-z>
- JINST 2023: <https://doi.org/10.1088/1748-0221/18/03/C03011>
- JINST 2023: <https://doi.org/10.1088/1748-0221/18/03/C03013>
- EPJ-C 2023: <https://arxiv.org/abs/2308.13231>
- HSTD23 proceedings in preparation

TJ-Monopix

- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167189>
- arXiv 2023 <https://doi.org/10.48550/arXiv.2301.13638>
- IEEE proceedings PACET2024 submitted

LF-Monopix

- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167224>
- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.166747>
- Vertex 2022 proceedings accepted, to be published
- Vertex 2023 <https://doi.org/10.22323/1.448.0043>
- HSTD23 Submitted, under revision

CACTUS

- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167022>
- NSS 2022: IEEE Trans.Nucl.Sci. 70 (2023) 11, 2471-2478

TJ 65nm

- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167213>

RD50-MPW

- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.166826>
- NIM A 2022 <https://doi.org/10.1016/j.nima.2022.167020>
- JINST 2023 <https://doi.org/10.1088/1748-0221/17/12/C12017>

- 27 publications
 - 9 new since Sept. 2023 published or in work
- Update of web-site and database in progress

WP5 meetings at:

<https://indico.cern.ch/category/13503/>

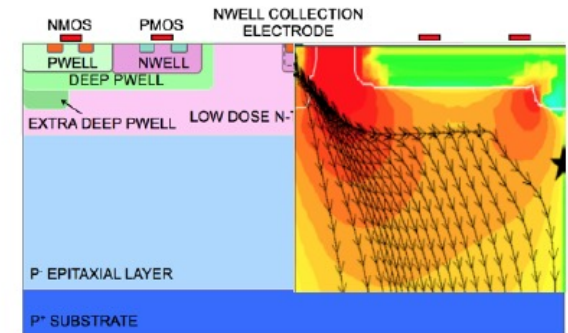
- Next slides are a brief summary of recent achievements as presented during our session yesterday
- See more details on the WP5 session agenda on indico:
 - <https://indico.cern.ch/event/1307202/>

Time	Activity	Speakers	Duration
14:30 → 18:00	Stream 2: WP5- Depleted monolithic active pixel sensors		
Conveners: Fabian Huegging (University of Bonn (DE)), Norbert Wermes (University of Bonn (DE)), Sebastian Grinstein (IFAE - Barcelona (ES))			
14:30	Recent Results on LF and TJ Monopix 2	Speaker: Fabian Huegging (University of Bonn (DE))	20m
	Monopixes_AIDAAn...		
14:50	Results on TJ Malta	Speaker: Marcos Vazquez Nunez (Univ. of Valencia and CSIC (ES))	20m
	AIDA_Catania_final...		
15:10	RD50-MPW Activities	Speakers: Chenfan Zhang (University of Liverpool), Chenfan Zhang (University of Liverpool (GB))	20m
	20240319_AIDAinn...		
15:30	DMAPS developments in TPSCo 65nm	Speakers: Ajit Kumar (IPHC Strasbourg), Jerome Baudot (IPHC - Strasbourg)	25m
	TPSCo65_AIDAinn...		
16:00	Coffee break		20m
16:20	Developments on ARCADIA	Speaker: Marco Mandurrino (Universita e INFN Torino (IT))	20m
	2024Mandurrino_Ai...		
16:40	Obelix for Belle II	Speakers: Ajit Kumar (IPHC Strasbourg), Jerome Baudot (IPHC - Strasbourg)	20m
	belle2-obelix-status...		
17:00	DMAPS Activities at PSI	Speaker: Aliakbar Ebrahimi (Paul Scherrer Institute (CH))	20m
	2024-03-19_Vertex...		
17:20	Recent developements for MiniCACTUS	Speakers: Prof. Philippe Schwemling (Université Paris-Saclay (FR)), Dr Yavuz Degerli (Université Paris-Saclay (FR))	20m
	AidaInnova_180324		

Tower 180 nm
TJ-MALTA-2&3
TJ-Monopix-2

Goal: large (1x2 cm² (Malta2) -> 3x2 cm² (Malta3)) radhard sensor/chip w/ small electrode and high granularity, HL-LHC-layer-5 compatible with low power **asynchronous** readout architecture. **Sensor&FE same as TJ-Monopix.**

CERN and others (Bonn, CPPM, Oxford ...)
- 180 nm technology -

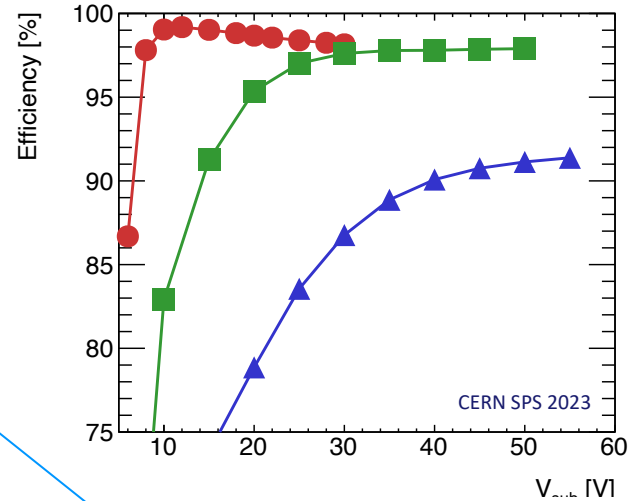
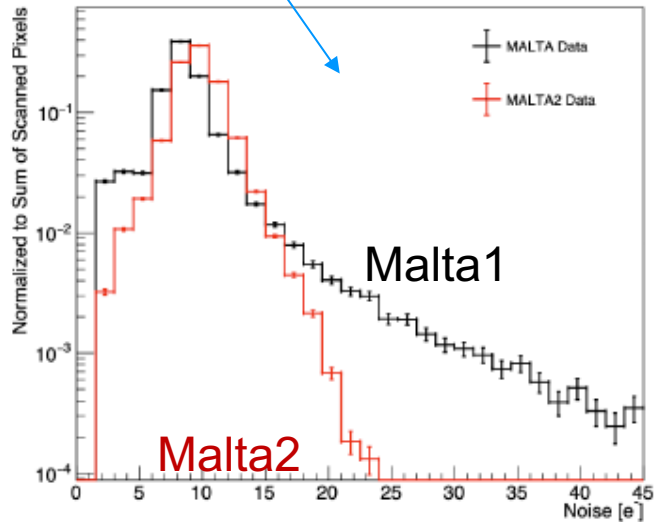


- main objective of TJ-MALTA2:
 - make design radhard ($> 1e15$ neq/cm²):
 - shape charge collection geometry
 - optimize FE against RTS noise
 - use high resistive Cz-Si substrate (100 μ m) rather than epi-Si (25 μ m).
 - improve asynchronous readout
- objective TJ-MALTA3:
 - exploit full reticle size: 3x2 cm²
 - improve on remaining MALTA2 issues
 - add 1.28 GHz local clock
 - target: mini-MALTA MPW in Q2 2023

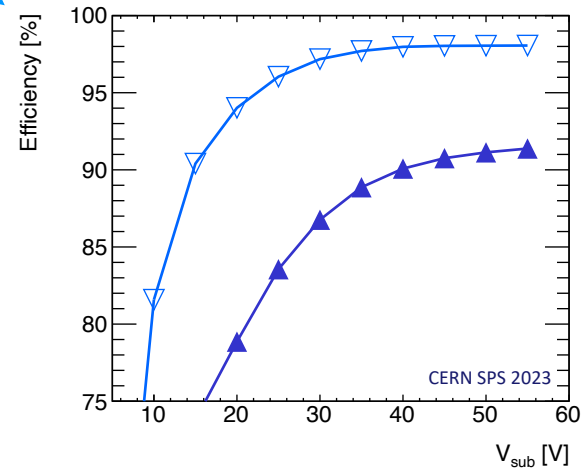
M. Vazques et al.

Goals of MALTA2 achieved:

- radhard up to $3E15$ n_{eq}/cm^2 (at least)
- Higher doping of n-layer helps
- RTS noise mitigated



- MALTA2**
Cz, 100 μ m, H-dop
back-metal, XDPW
- 1×10^{15} 1 MeV n_{eq}/cm^2
 - 2×10^{15} 1 MeV n_{eq}/cm^2
 - ▲ 3×10^{15} 1 MeV n_{eq}/cm^2

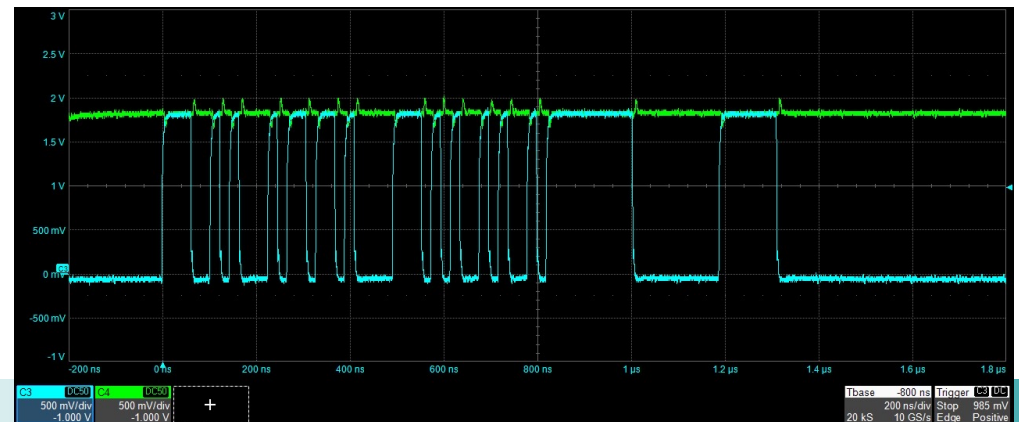
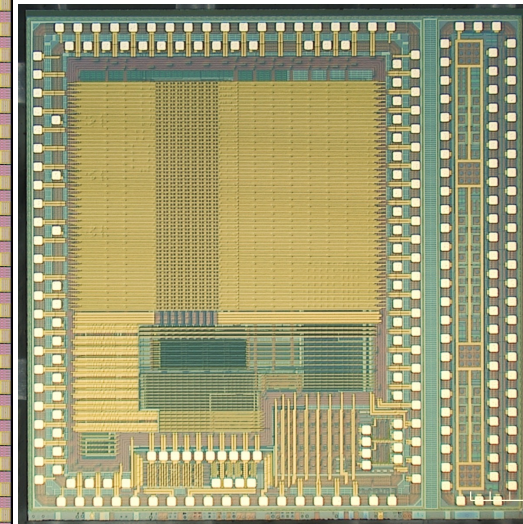
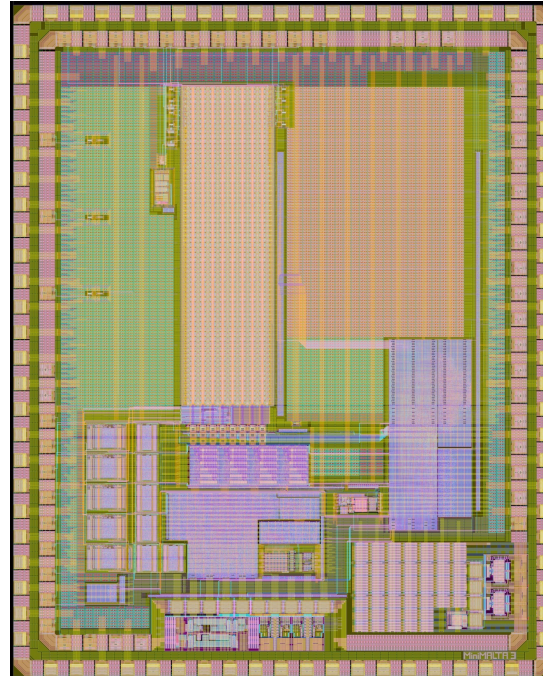


- MALTA2**
Cz, 100 μ m
back-metal, XDPW
 3×10^{15} 1 MeV n_{eq}/cm^2
- ▽ VH-dop
 - ▲ H-dop

- excellent matrix homogeneity

M. Vazques et al.

- Mini-MALTA 3
 - 5x4 mm² demonstrator for full MALTA3
 - Same FE as MALTA2
- Chip arrived in late 2023
- Chip is alive and systematic testing including test beams starts now



M. Vazques et al.

Goal: mature large ($2 \times 2 \text{ cm}^2$) high granularity (small electrode) fully functional, HL-LHC compatible (5th layer) DMAPS sensor with column drain readout, w/ low noise and low power consumption

	TJ-Monopix1	TJ-Monopix2
Chip Size	1x2 cm ² (224x448 pix)	2x2 cm ² (512x512 pix)
Pixel size	36 × 40 μm ²	33.04 × 33.04 μm ²
Total matrix power	130 mW/cm ²	170 mW/cm ²
Noise	≅ 11 e ⁻	< 8 e ⁻ (improved FE)
LE/TE time stamp	6-bit	7-bit
Threshold Dispersion	≅ 30 e ⁻ rms	< 10 e ⁻ rms (improved FE + tuning)
Minimum threshold	≅ 300 - 400 e ⁻	< 200 e ⁻
In-time threshold	≅ 350 - 450 e ⁻	< 250 - 300 e ⁻
Efficiency at 10 ¹⁵ n _{eq} /cm ² , 30 μm epi	≅ 87 %	> 97 %
Efficiency at 10 ¹⁵ n _{eq} /cm ² , Cz	≅ 98.6 %	> 99 %

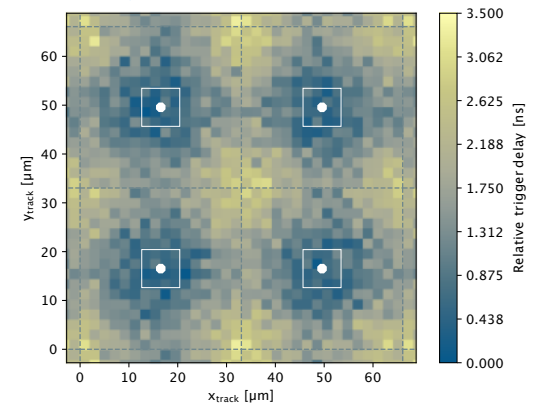
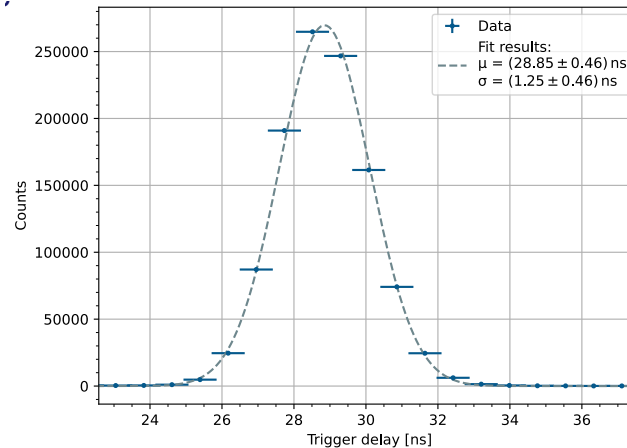
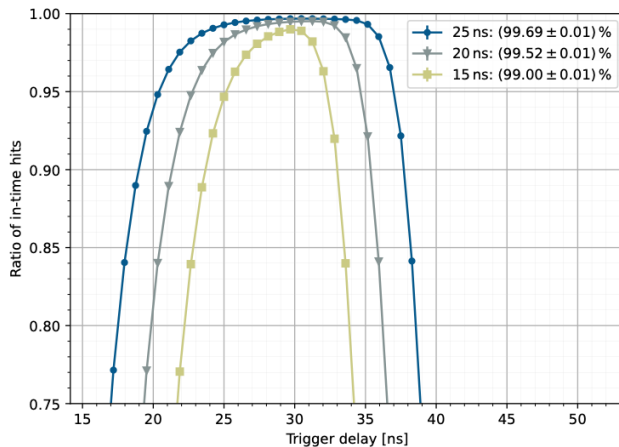
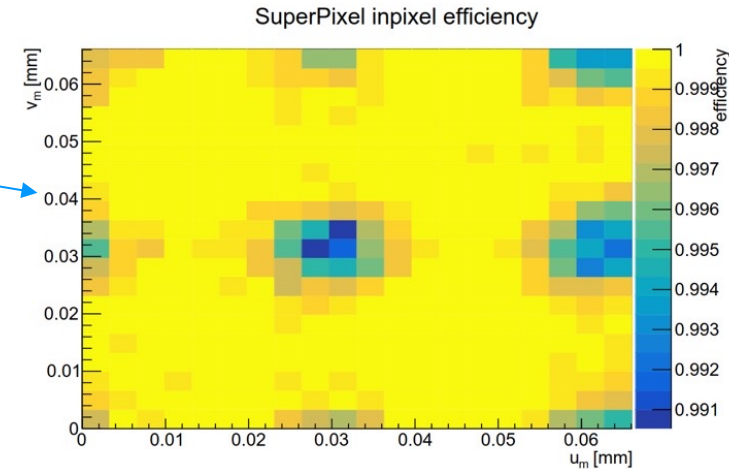
- Clear improvements wrt TJ-M1 before and after irradiation

Bonn, CERN, CPPM, IRFU
- 180 nm technology -

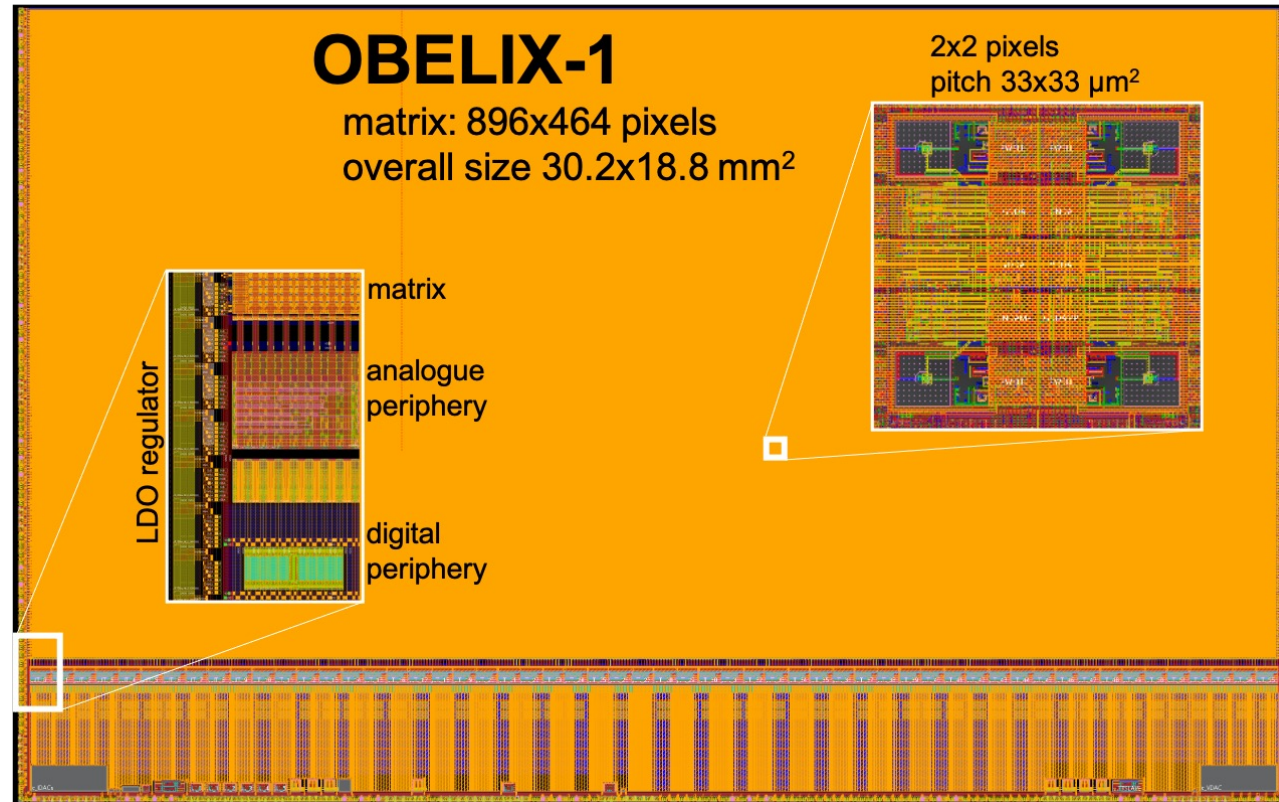
- sensor and chip working
- assembly problems (wire bonding sensibility) reduce yield, is now manageable, but still problematic
- a temporary major problem at 5 MHz BC-ID clock interfering now understood and circumvented
- characterisation finally in full swing
- baseline for Belle II VTX upgrade → Obelix chip:
 - Uses analog part from TJ Monopix 2
 - New digital periphery with several additional features

Most recently added detailed timing performance and post irradiation measurements:

- >99% eff. after $5E10^{14}n_{eq}/cm^2$ irradiated with 24 MeV p
- ~1-2 ns time resolution limited by TDC (1.5625 ns bin size, 93.7 ps time resolution from FE)
- > 99% in-time efficiency for 25 ns window and for 15 ns window for epi-Si (26 μ m depl. volume)
- Delay difference of up to 3.5 ns depending on in-pixel track position



Pitch	33 μm
Signal ToT	7 bits
Integration time	50 To 100 ns
Time stamping	~ 5 ns for hit rate < 10 MHz/cm ²
Hit rate max for 100% eff.	120 MHz/cm ²
Trigger handling	30 KHz with 10 μs delay
Trigger output	~ 10 ns resolution with low granularity
Power (with hit rate)	120 to 200 mW/cm ² (1 to 120 MHz/cm ²)
Bandwidth	1 output 320 MHz



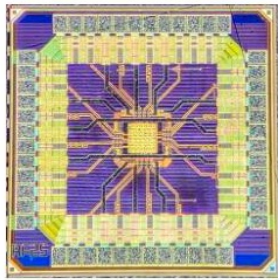
TPSCo 65 nm process of **Tower**
(new window of opportunity)

Tower 65nm

Goal: exploring the new technology (large collaboration effort, CERN + 24 institutions) including stitching, small electrode designs

1+2 submissions so far: MLR1 (2020), ER1 (2022) each containing several structures and designs
ER2 is expected for 2025

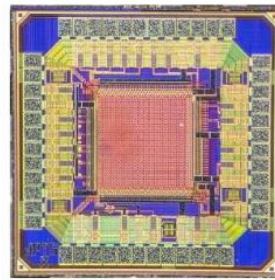
APTS Analogue Pixel Test Structure



Matrix: 6x6
Readout: analogue readout of 4x4
Pitch: 10,15,20,25 μm
Process: all 3 variants

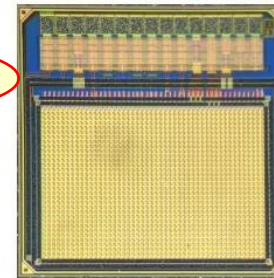
1.5 mm

DPTS Digital Pixel Test Structure



Matrix: 32x32
Readout: async. digital with ToT
Pitch: 15 μm
Process: 1 variant (modified with gap process)

CE-65 Circuit Exploratoire 65

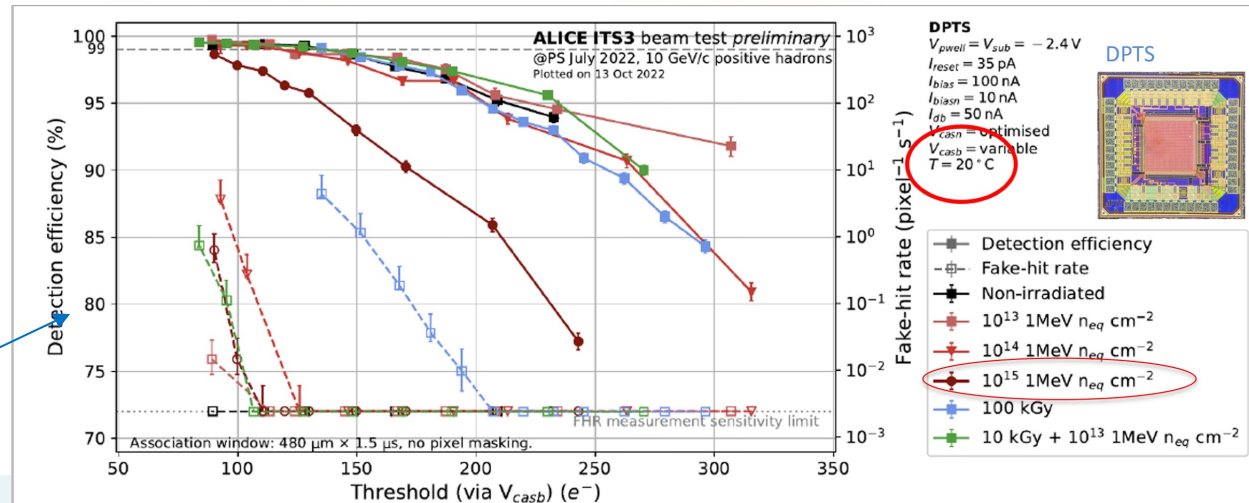


Matrix: 48x32
Readout: rolling shutter analog
Pitch: 15, 25 μm
Process: 1 variant (modified with gap process)

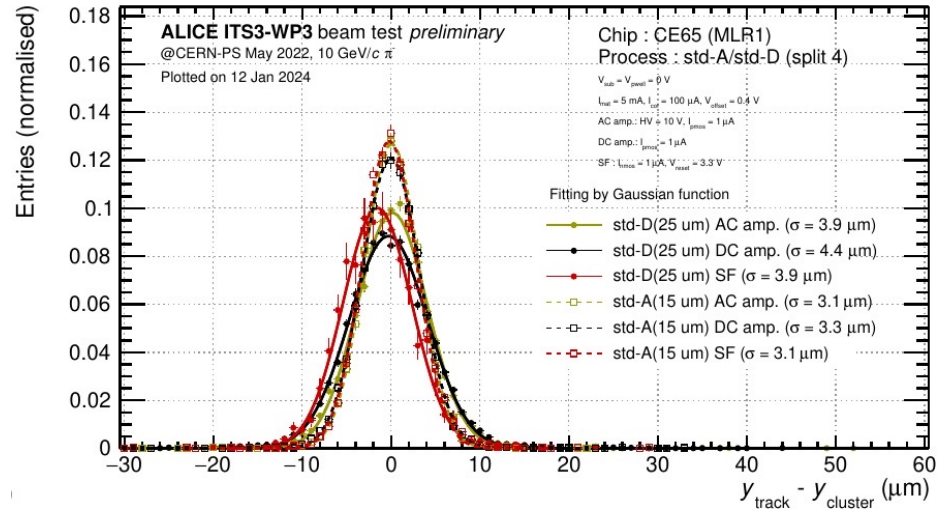
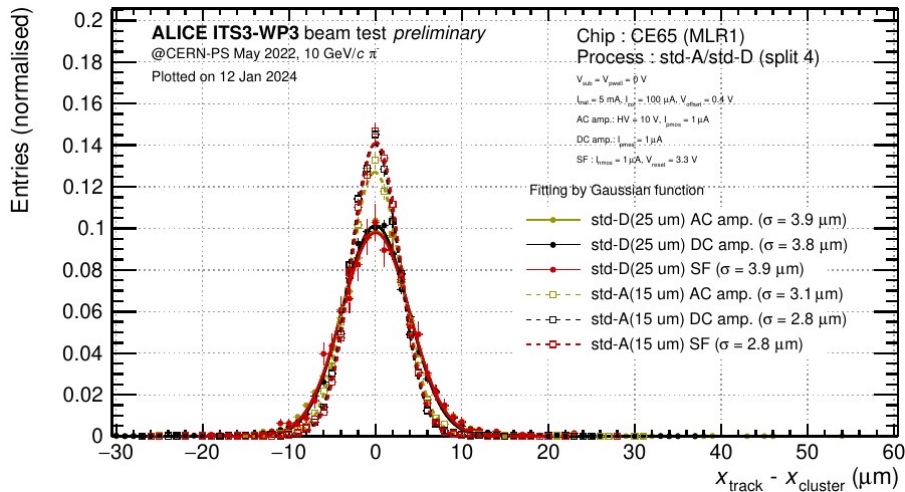
from MLR1

promising results from MLR1

- leakage cur. ✓
- Testbeam with DPTS (digital 15 μm) proved that process modification works & radiation tolerance $> 10^{15} n_{\text{eq}}/\text{cm}^2$



Detailed position resolution studies done CE65v1/v2 chip family form MLR1 and ER1



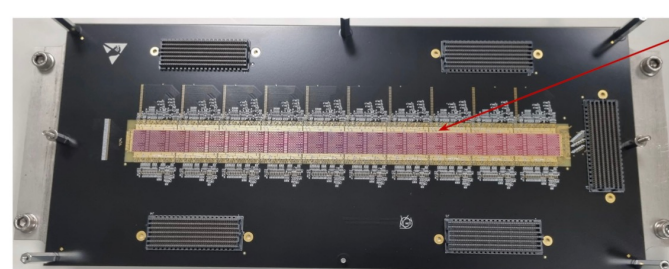
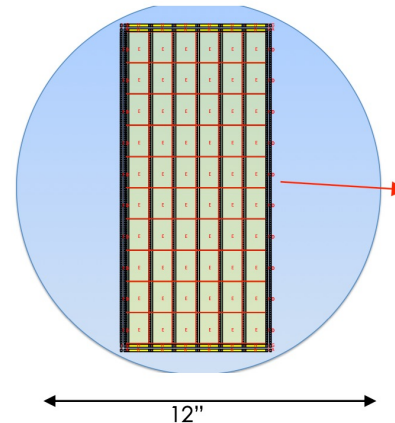
Very good results achieved:

- spatial resolution of $\sim 2.7 \pm 0.3\text{ }\mu\text{m}$ for standard 25 μm pixel
- spatial resolution of $\sim 1.3 \pm 0.3\text{ }\mu\text{m}$ for standard 15 μm pixel
- to be compared with DPTS with modified process and 15 μm pixel: 4 – 4.2 μm

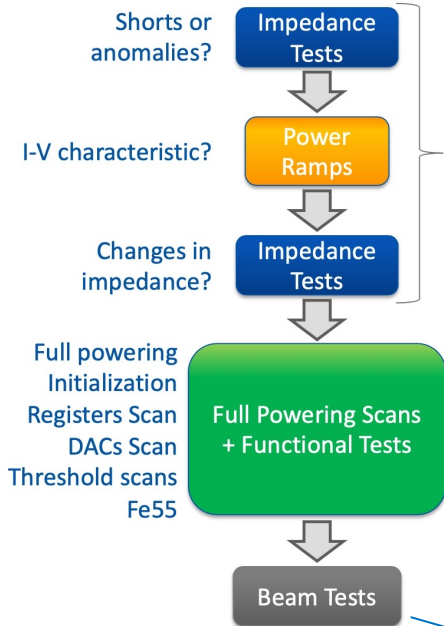
J. Baudot, A. Kumar et al.

2nd submission: Engineer Run 1 (ER1)

- Main goal = exercise stitching (in 1D) to assess yield
- Submission November 2022
- Back from fab April 2023
- 2 long (~26 cm) sensors
 - **MOSS**: priority-encoder readout (ALPIDE-like)
 - 1.4 cm wide
 - 18 & 22.5 μm pitch
 - **MOST**: low power asynchronous readout
 - 0.25 cm wide
- Many (51) **chipelets**
 - Pixel prototypes
 - SEU test chips
 - Functional blocks (PLL, serial links)
- New metal staks
- New methodology for submission
 - Digital-on-top



Test in preparation



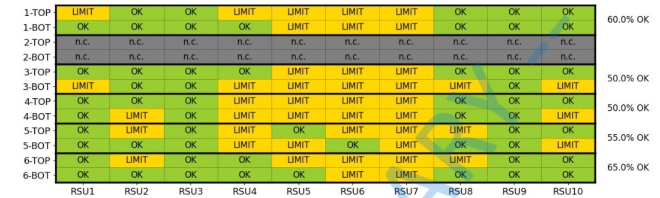
Ramp supplies slowly and monitor currents

OK -> all supplies ramped to full voltage and currents less than compliance *limit*

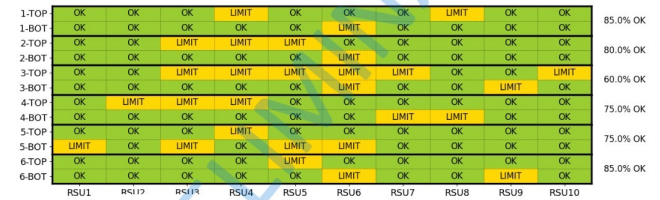
Wafer maps reconstructed from power ramps data of MOSS on carriers

Wafer to wafer differences

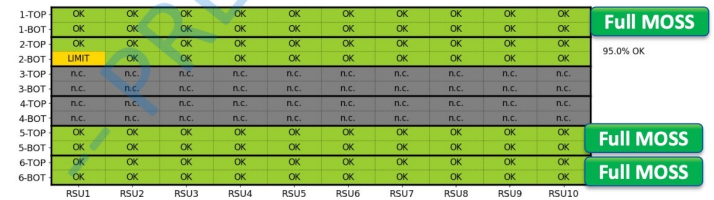
Detailed investigation of units with high current ongoing



WAFER 23 - Power Ramp - 92/120=76.67% HUS OK



WAFER 24 - Power Ramp - 79/80=98.75% HUS OK



Full MOSS

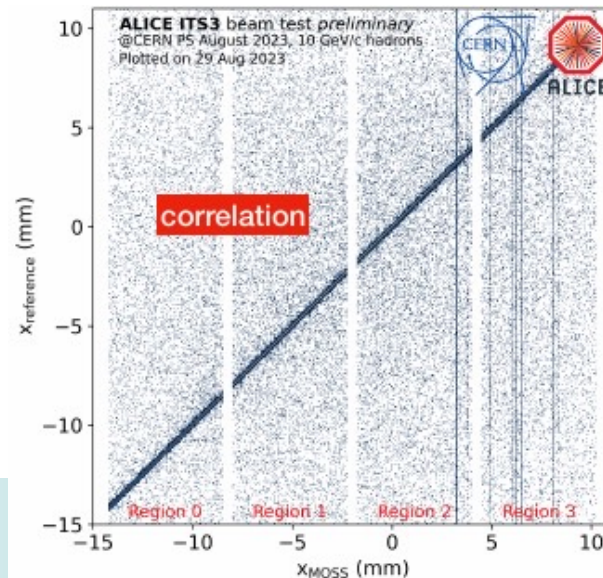
95.0% OK

Full MOSS

Full MOSS

Stitched sensor MOSS from ER1:

- Design is functional
- Sensor works – 26 cm long!
- Learning about yield and wafer-to-wafer variations



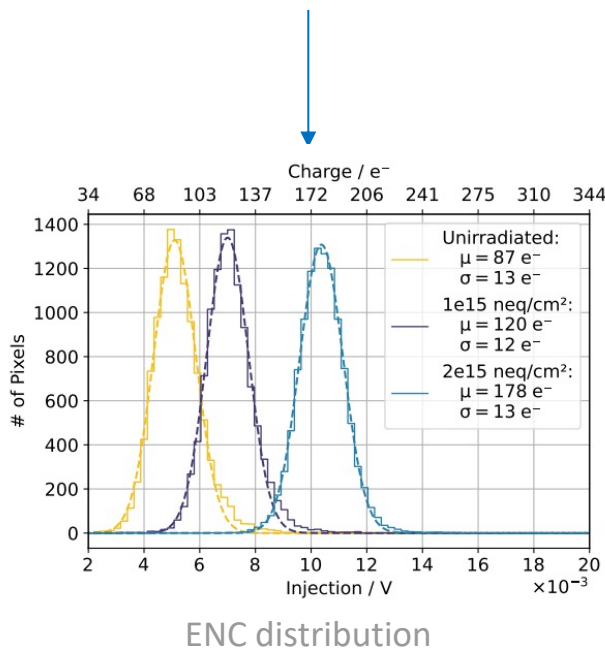
LFfoundry 150 nm

- LF-Monopix-2
- RD50 – MPW2/3
- CACTUS

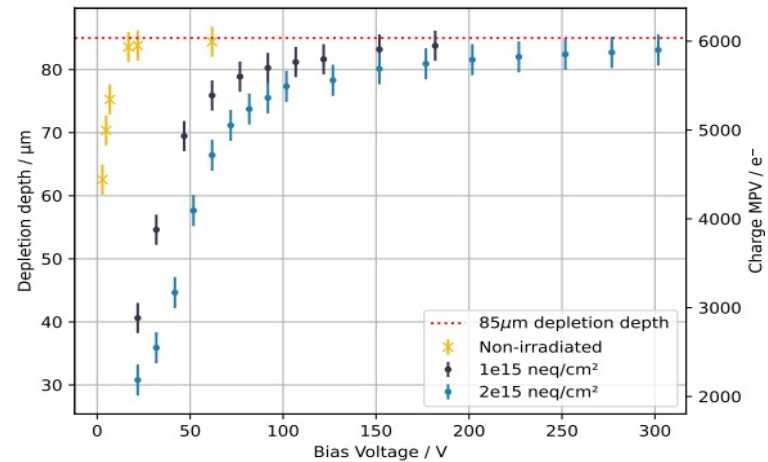
Goal: mature large ($1 \times 2 \text{ cm}^2$) (very) radhard, large electrode fully functional, HL-LHC compatible (5th layer) DMAPS sensor with column drain readout

irradiated devices (1 and $2 \times 10^{15} \text{ neq/cm}^2$ @ Bonn Cyclotron)

- no significant degradation at this level except for leakage current increase



Calibrated charge MPVs



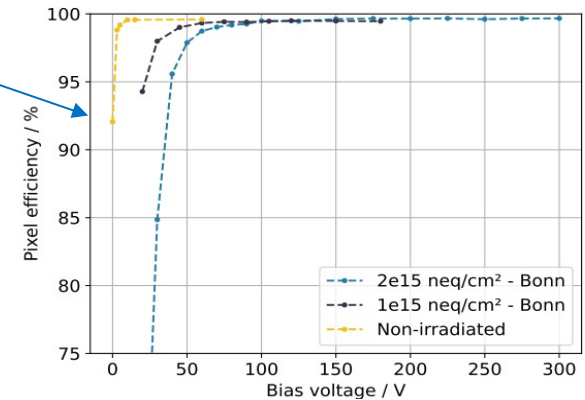
- fully depleted @ $\sim 200 \text{ V}$ bias (15 V unirradiated)

Lars Schall, C. Bispin, et al.

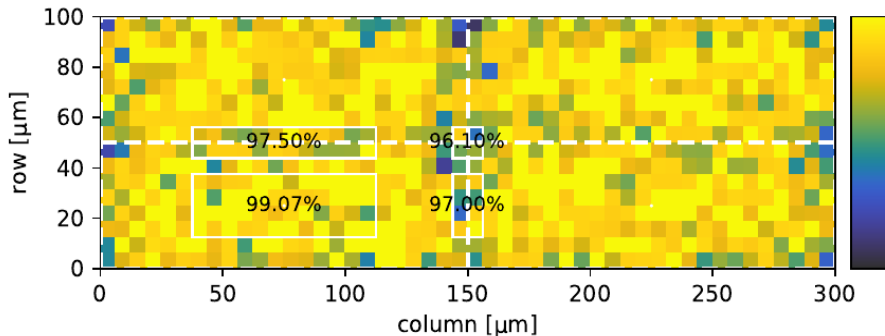
Goal: mature large ($1 \times 2 \text{ cm}^2$) (very) radhard, large electrode fully functional, HL-LHC compatible (5th layer) DMAPS sensor with column drain readout

- intensive test beam characterisations
- very high (>99%) efficiency (in-time) after 1 and $2 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$
- ~no efficiency degradation wrt unirradiated devices
- **New**: devices irradiated to $2 \times 10^{15} \text{ n}_{\text{eq}}$ tested:
 - still >99% efficiency but more pixel disabled due to leakage current induced ENC increase, higher gain of pre-amp helps for in-time eff.

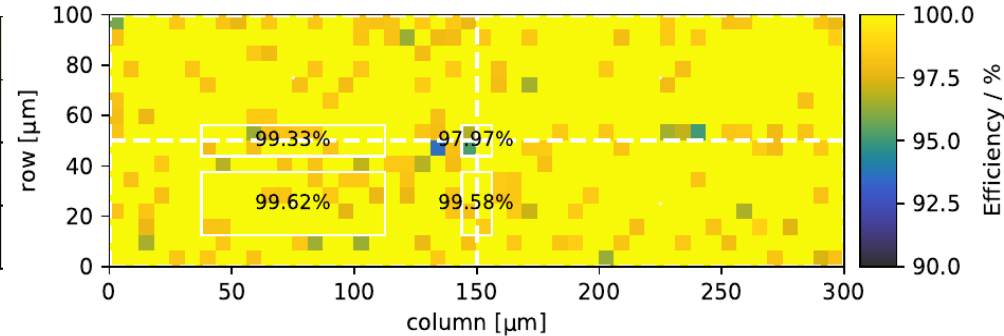
Hit-detection efficiency vs bias voltage



In-pixel, in-time efficiency
(mean 98.35% @ $2 \times 10^{15} \text{ neq}/\text{cm}^2$)



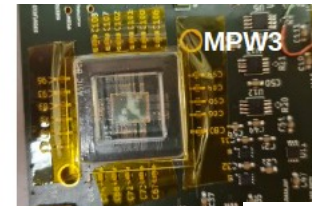
In-pixel, in-time efficiency
(mean 99.60% @ $2 \times 10^{15} \text{ neq}/\text{cm}^2$)



Goal: series of MPWs (1 ... 4) to achieve very small pixels ($60 \times 60 \mu\text{m}^2$) radhard @ HL-LHC level 5th layer by large electrode design (all electronics inside deep well)

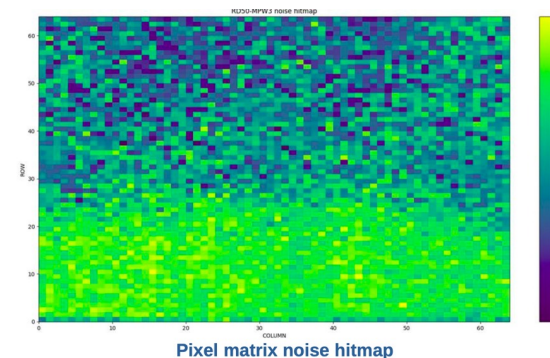
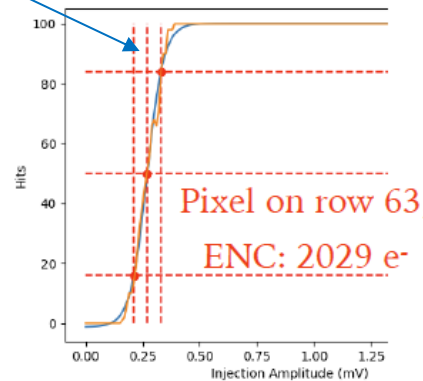
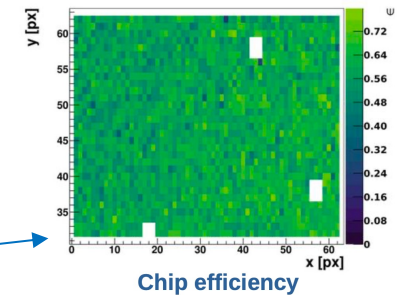
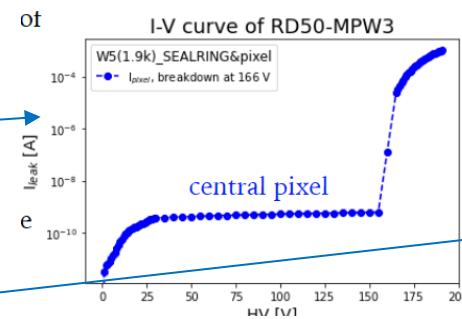
MPW2: small prototype

- pixels: $60 \times 60 \mu\text{m}^2$
- in-pix CSA + discriminator, analog R/O
- testbeams performed
- charge collection ok



MPW3: added digital R/O (column drain)

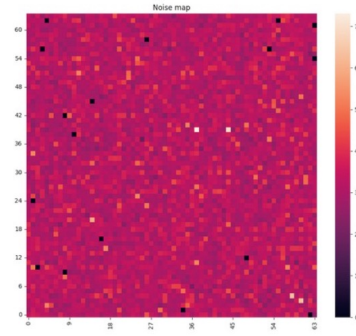
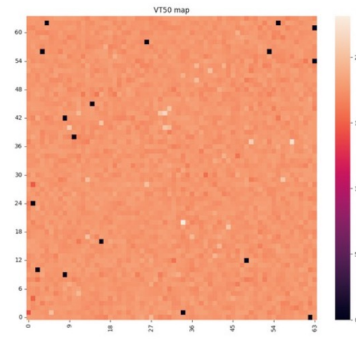
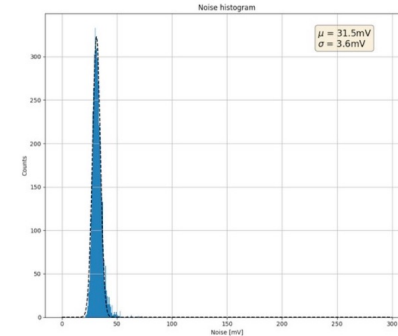
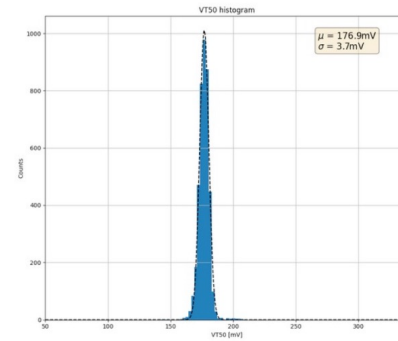
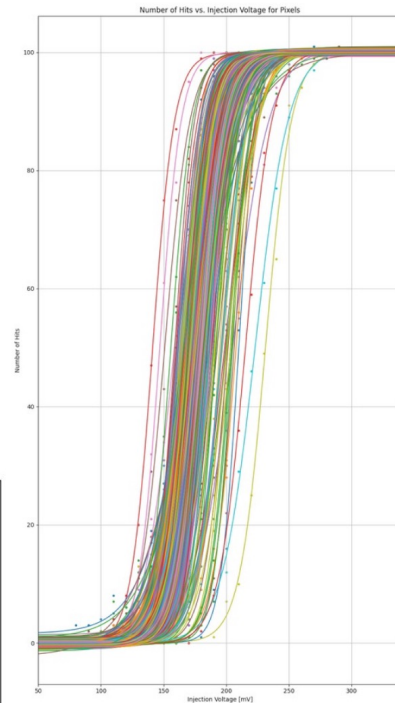
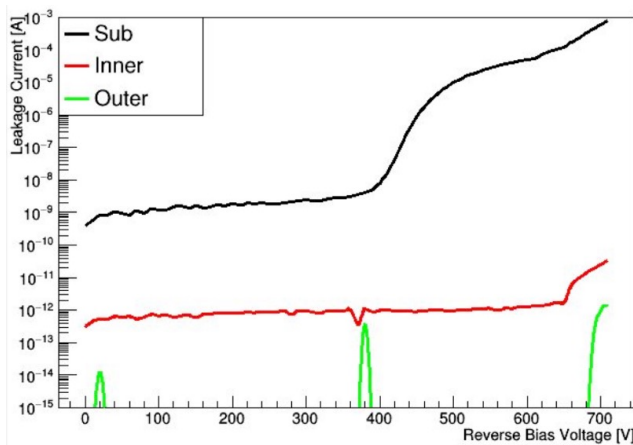
- $V_{\text{breakdown}} \sim 150\text{V}$
- very high noise ($> 2000 \text{ e}$) due to noise coupling from digital periphery
- Poor test beam efficiency due to high thresholds



MPW4 (2023/24): backside processing to improve radiation hardness, eliminate high noise and increase breakdown

MPW4 (2023/24):

- Initial tests indicate that noise elimination and breakdown voltage increase was achieved
- Tests with backside processed wafers proved improved leakage current behaviour

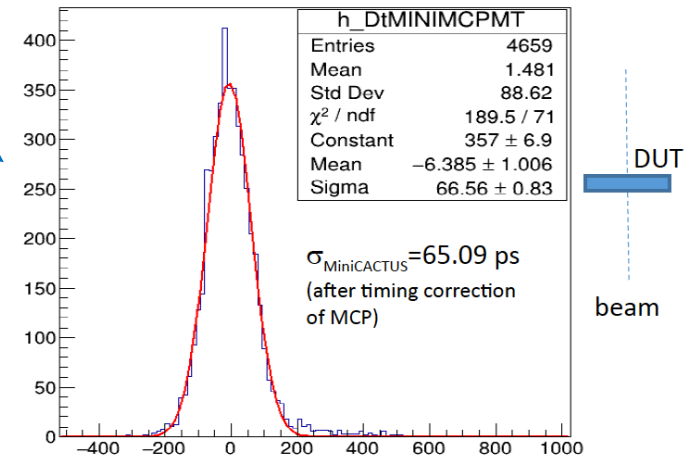


- ENC of $200e^-$ over whole matrix and small threshold dispersion

Goal: Develop CMOS pixels for timing applications (~50 ps)

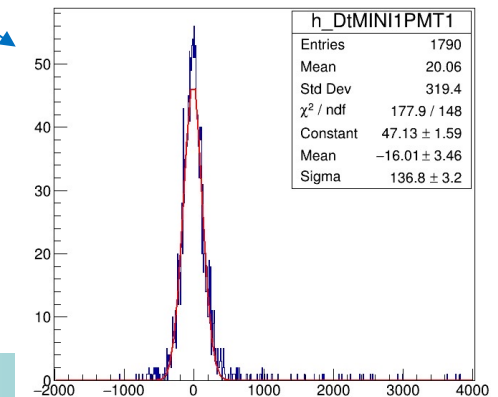
Mini CACTUS = small prototype to address limitations of CACTUS (low S/N)

- 65 ps mip time resolution achieved in test beams
- compared calibrations and resolutions using photons of different energies (^{241}Am and @SOLEIL)
 - calibrations ✓
 - σ_t for photons (understandably) worse (320 ps)
- characterisation after $1e14$:
 - Time resolution worsens at room temperature but with low leakage current at -15°C recovers



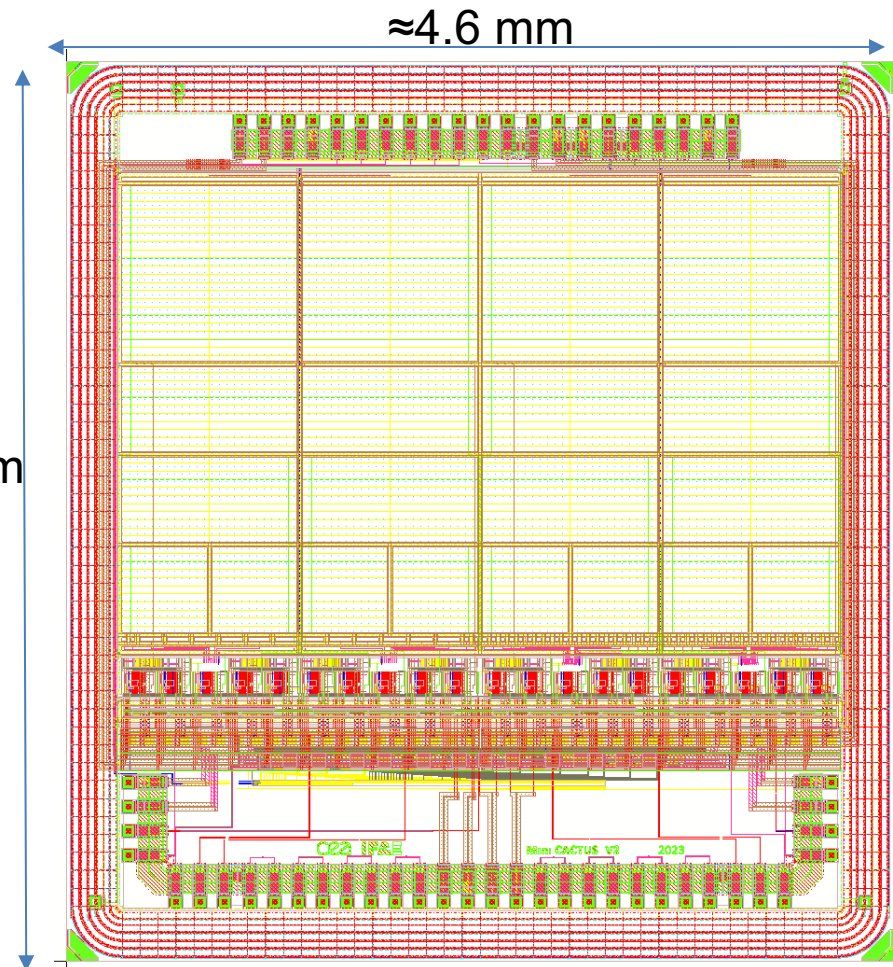
Sensor	HV bias (V)	Conditions	Temp. (°C)	Time res. (ps)	MPV (mV)
Unirradiated 300 u	400	testbeam, MCPMT time reference	room	78.97 ± 1.36	201.9 ± 0.5
Unirradiated 300 u	400	90Sr, PMT time reference*	room	104.5 ± 2.30	195.7 ± 2.3
Unirradiated 300 u	280	testbeam, MCPMT time reference	room	89.11 ± 1.56	200.9 ± 0.5
Irradiated 300 u	280	90 Sr, PMT time reference	20	108.2 ± 3.2 (PMT subt.)	108.2 ± 3.2
Irradiated 300 u	320	90 Sr, PMT time reference	20	132.9 ± 5.0 (PMT subt.)	113.5 ± 0.8
Irradiated 300 u	320	90 Sr, PMT time reference	-15	87.9 ± 4.7 (PMT subt.)	132.7 ± 0.6

DT PMT1-MIN1 (ps)



- ~ 2 times larger than MiniCACTUS
- 0.5 mm x 1 mm (baseline), 1 mm x 1 mm and 0.5 mm x 0.5 mm diodes
- 50 μm x 150 μm and 2 50 μm x 50 μm small test diodes
- 3 different preamps
- New multistage discriminator with **programmable hysteresis**
- Improved layout for better mixed-signal coupling rejection
- **CEA-IRFU & IFAE-Barcelona** coll.
- Submitted in May 2023, waiting for samples to
- come back from post-processing

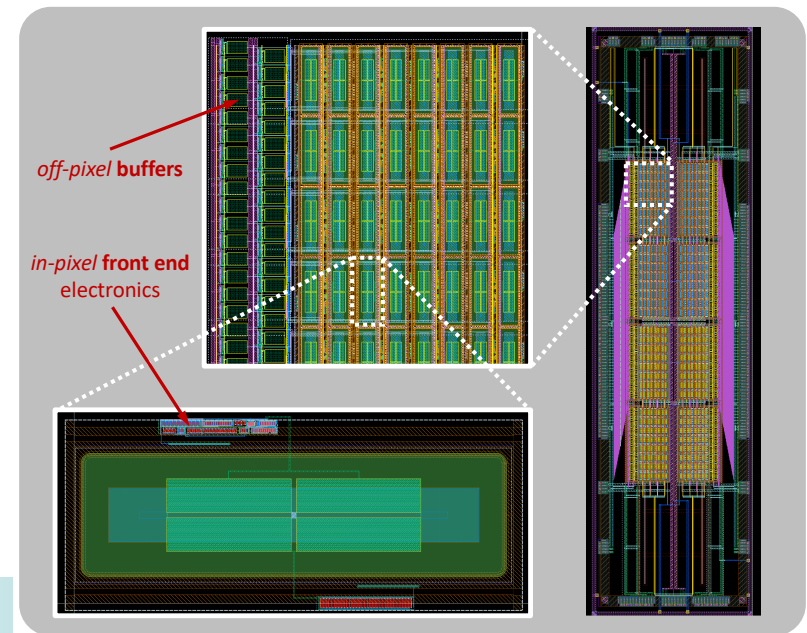
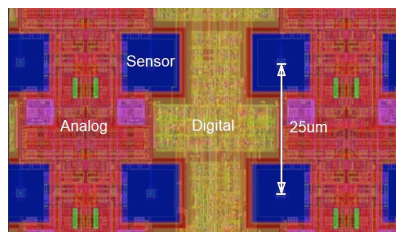
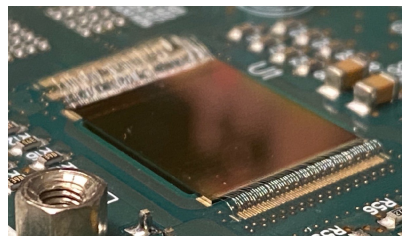
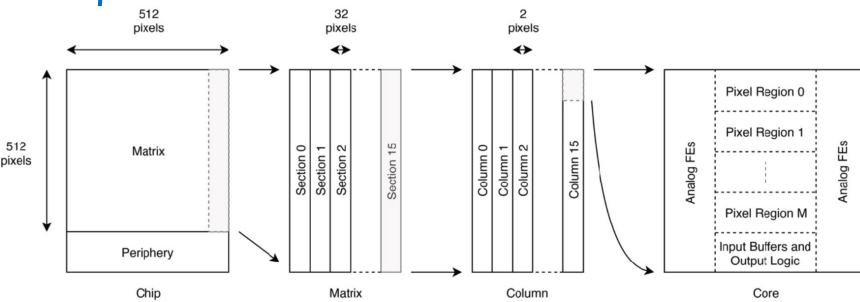
$\approx 5 \text{ mm}$



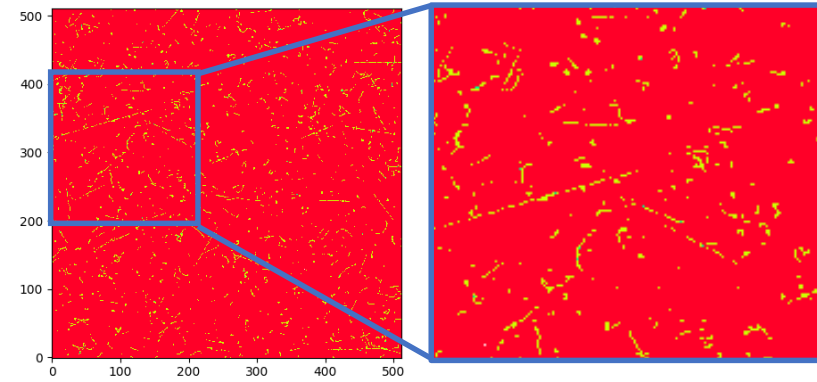
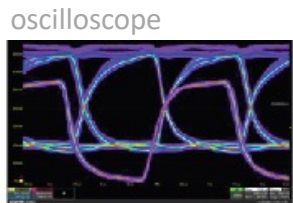
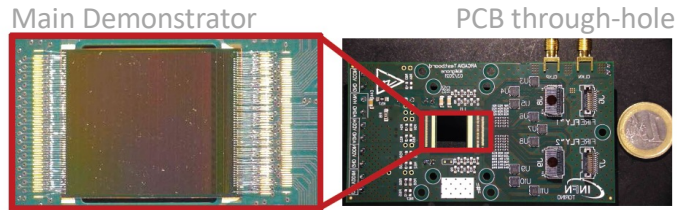
LFfoundry 110 nm
ARCADIA

Goal: Develop DMAPS technology platform in 110 nm technology. Largely funded by INFN. Targeting small pixels, very low power, various thicknesses

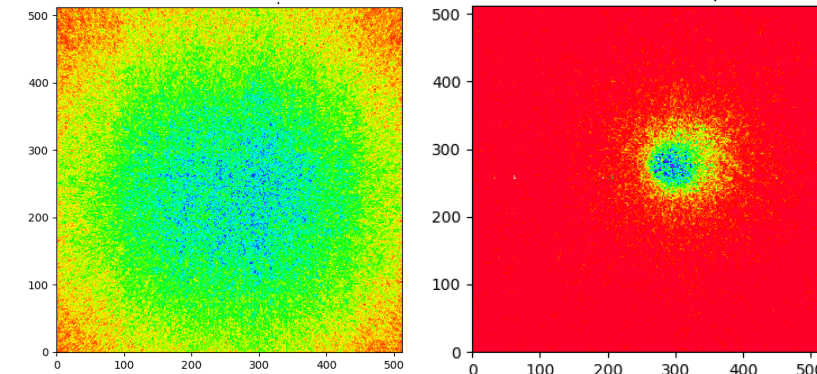
- MD3 main-demonstrator with system-grade full chip Fully Depleted MAPS (FDMAPS with 512x512 pixel matrix, pitch 25 μm , low power, high event rate)
- Scalable FDMAPS architecture with very low power of 10 mW/cm²
- adding gain layer for LC3 (MADPIX), small prototype (4 x 16 mm²)
- Structures from both are available and first results looks reasonable



Main Demonstrator - acquisition setup



Cosmic rays acquisition (4h)



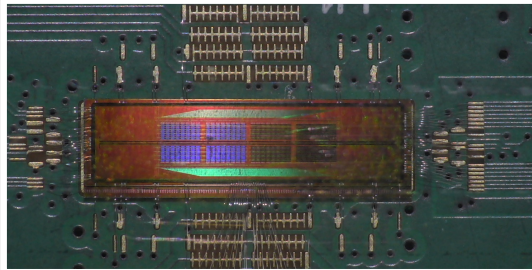
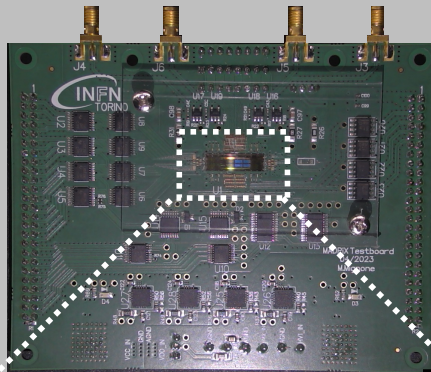
^{90}Sr beta source (1cm²) 8 mm from the sensor surface

Collimated ^{90}Sr beta source
Collimator diameter: 1mm

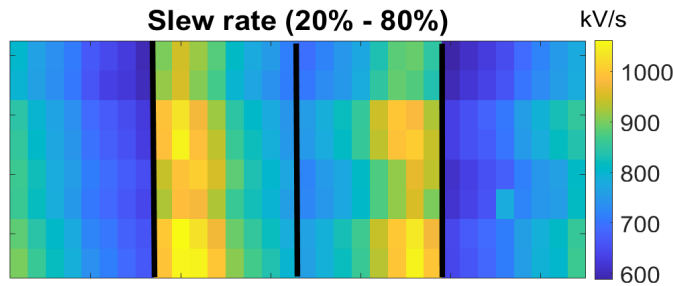
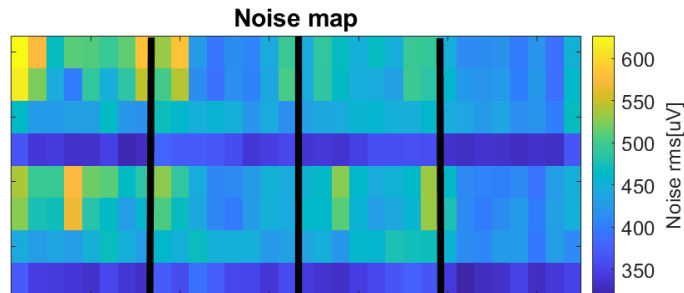
- Total power consumption: 10 mW/cm² at low event rates
- Design specification: 20 mW/cm² at rates up to 100 Mevents/cm²

M. Mandurrino et al.

MadPix testboard

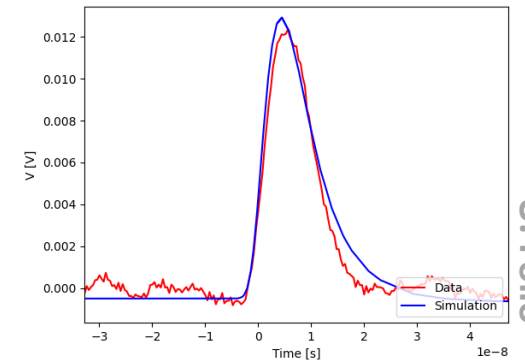
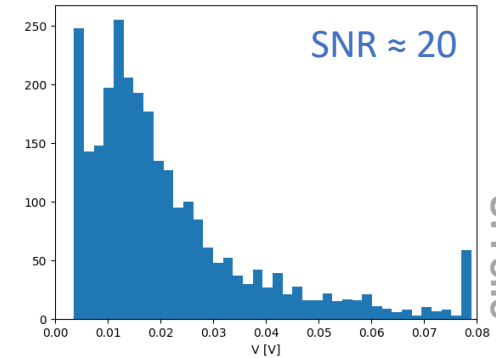


Noise and slew-rate characterization with external test-pulse injection



U. Follo

First data with beta source (^{90}Sr)



U. Follo

U. Follo

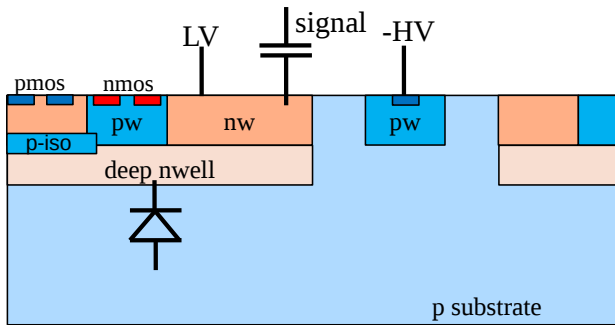
- But gain layer turned out to be too low (~ 3 instead of 10 – 30) due to mismatch in p-gain implant energy
- Will be fixed now with new short loop engineering run

LFoundrxy 110 nm, TSI

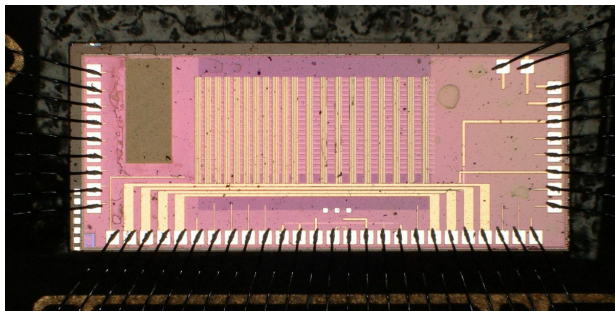
PSI developments

Goal: Generic R&D on DMAPS with TSI and technology platform in LF 110 nm provided by ARCADIA

- 2 PSI TSI MAPS chips designed – TSI-RS4, large collecting electrode
- LF 110 prototypes designed and manufactured using the ARCADIA platform (MoTiC A & B), small collecting electrode, TDC shared by 4 pixel

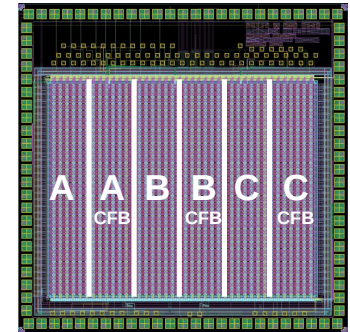


TSI-RS4



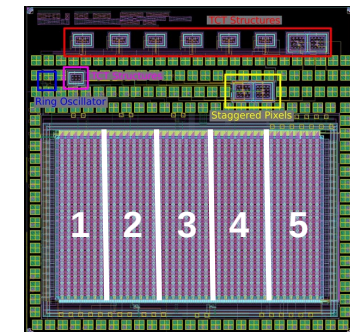
20 columns, 20 rows
50 x 100/150 μm^2

Same sensor
6 different amplifiers
80 columns, 64 rows
50 x 50 μm^2



MoTiC A

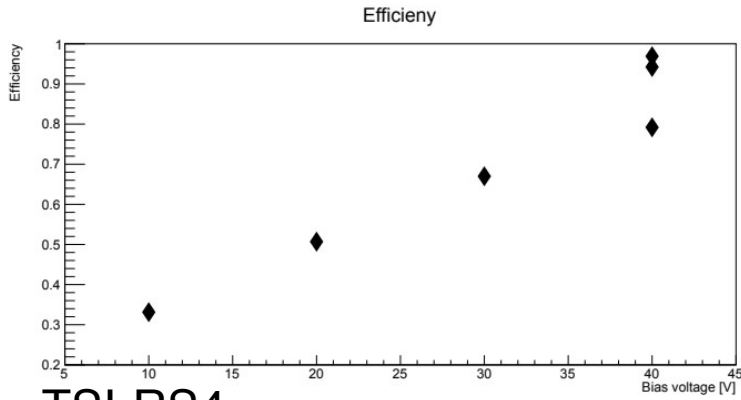
Same amplifier (C)
5 different sensors
80 columns, 48 rows
50 x 50 μm^2



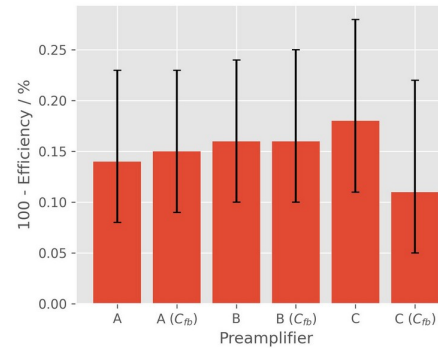
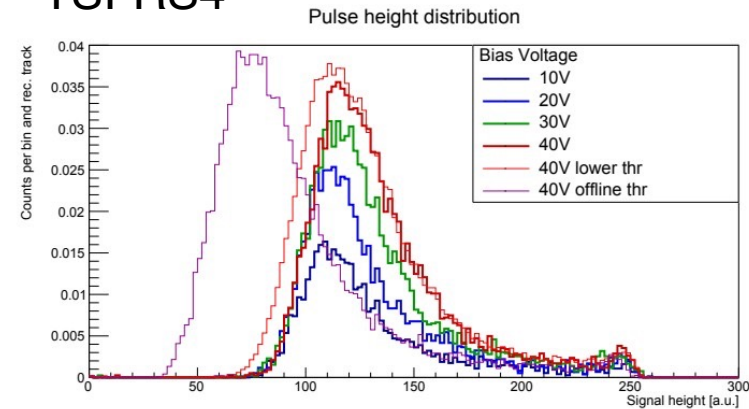
MoTiC B

Goal: Generic R&D on DMAPS with TSI and technology platform in LF 110 nm provided by ARCADIA

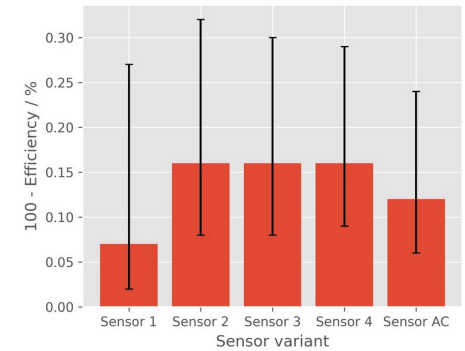
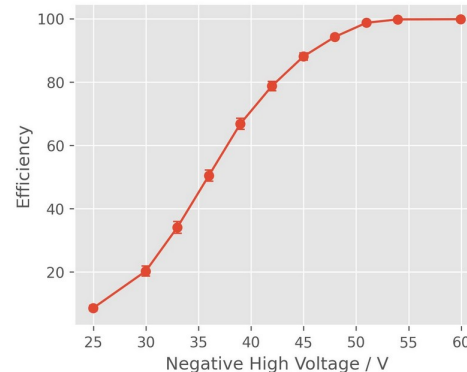
- Encouraging results achieved but still early stage
- TSI developments stopped due to foundry finishing this node



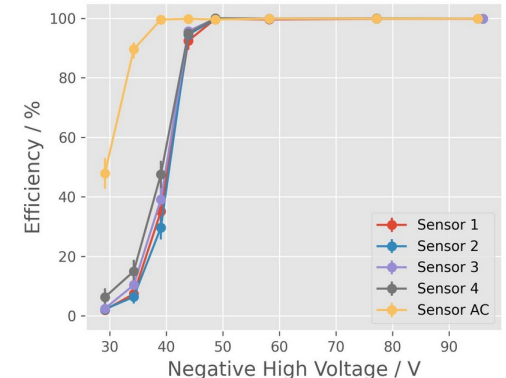
TSI-RS4



MoTiC A



MoTiC B



- ❑ Lots of activity at all fronts: *high granularity, radiation hardness and timing*
- ❑ Fabrication of devices completed in all lines
- ❑ All research lines are currently intensively characterizing their devices
- ❑ 2 Milestones (MS18, MS20) and 1 Deliverable (D5.1) achieved
- ❑ Next Milestone MS19 & Deliverable D5.3 due in April but sufficient material is already available
- ❑ Many publications

BACK UP SLIDES

One contact person per institution:

Carlos Solans <carlos.solans@cern.ch> – CERN
Eva Vilella Figueras <vilella@hep.ph.liv.ac.uk> – Liverpool
Jerome Baudot <jerome.baudot@iphc.cnrs.fr> – IPHC
Thomas Bergauer <Thomas.Bergauer@cern.ch> – HEPHY
Francesco Forti <Francesco.Forti@pi.infn.it> – Pisa
Marlon Barbero <barbero@cppm.in2p3.fr> – CPPM
Daniela Bortoletto <Daniela.Bortoletto@physics.ox.ac.uk> – Oxford
SCHWEMLING Philippe <Philippe.Schwemling@cea.fr> – IRFU
"C. Marinas" <cmarinas@ific.uv.es> – IFIC
Manuel Dionisio da Rocha Rolo <darochar@to.infn.it> – Torino
Attilio Andreazza <attilio.andreazza@mi.infn.it> – Milano
Valerio Re <valerio.re@unibg.it> – Pavia
F. Hügging <huegging@physik.uni-bonn.de> – Bonn
S. Grinstein <sgrinstein@ifae.es> – Barcelona

- Let us know of changes above.
- The AIDAinnova-WP5@cern.ch mailing list is used for general announcements and information.